

In the Claims:

1. (Currently Amended) A single crystal semiconductor body having a trench with first sidewall portions of said trench disposed in a first different crystallographic plane ~~planes~~ of the body, and second sidewall portions of said trench disposed in a second crystallographic plane, said first such sidewall portions having thereon substantially uniformly thick, thermally grown, silicon dioxide material thermally grown at a first rate to a uniform thickness, and said second sidewall portions having thereon silicon dioxide material thermally grown to substantially said same uniform thickness at a second rate.

2.-4. (Canceled)

5. (Currently Amended) A single crystal semiconductor body comprising:
a trench formed in a surface of said single crystal semiconductor body, said trench having sidewall portions being disposed in different crystallographic planes of the body;
first sidewall portions of said trench disposed in a first one of the different crystallographic planes;
a first layer of silicon dioxide material grown on said first sidewall portions at a first rate and to a first thickness when subjected to a thermal oxidation process;
second sidewall portions of said trench disposed in a second one of the different crystallographic planes; and
a second layer of silicon dioxide grown on said second sidewall portion at a second rate and on said first layer of said silicon dioxide material at a rate slower than said second rate wherein said first and second sidewall portions of the trench are subjected to a thermal oxidation process such that the thickness of said second layer of silicon dioxide on said second sidewall

2004 P 51343 US

portions is substantially equal to the thickness of both said first and second layers of silicon dioxide on said first sidewall portions.

6. (Currently Amended) A single crystal semiconductor body comprising:

a trench formed in a surface of said single crystal semiconductor body having sidewall portions thereof of said trench disposed in [[a]] different crystallographic planes of said semiconductor body;

a relatively thin material on selected sidewall ~~ones of the surface portions, said selected ones of the surface portions~~ of said trench residing in a first one of said different crystallographic planes;

a layer of silicon dioxide grown over said relatively thin material at a first rate by a thermal oxidation process to a selected thickness; and

said silicon dioxide grown at a second rate during said thermal oxidation process on unselected sidewall surface portions of said trench residing in a second one of said ~~in a different crystallographic plane~~ planes, said second rate faster ~~different~~ than said first rate such that the resulting thickness of said silicon dioxide grown over both the selected sidewall ~~surface~~ portions and the unselected sidewall ~~surface~~ portions are substantially uniform.

7. (Currently Amended) The semiconductor body of claim 5 wherein said first sidewall portions are disposed in the <110> ~~<100>~~ crystallographic plane and said second sidewall portions are disposed in the <100> ~~<110>~~ crystallographic plane.

8. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material is silicon nitride.

9. (Previously Presented) The semiconductor body of claim 6 further comprising another layer of silicon dioxide formed on said relatively thin material such that said another layer of silicon dioxide and said layer of silicon dioxide grown over said relatively thin material have a combined thickness substantially the same as the thickness of said layer of silicon dioxide grown on said unselected surface portions of said semiconductor body.
10. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material is less than approximately 20 Angstroms.
11. (Previously Presented) The semiconductor body of claim 6 wherein the relatively thin material forms a layer which is thinner than the corresponding oxide layer grown on the selected and unselected surface portions.
12. (New) The semiconductor body of claim 6 wherein said first sidewall portions are disposed in the $\langle 110 \rangle$ crystallographic plane and said second sidewall portions are disposed in the $\langle 100 \rangle$ crystallographic plane.
13. (New) The semiconductor body of claim 1 wherein said trench is oval shaped.
14. (New) The semiconductor body of claim 5 wherein said trench is oval shaped.
15. (New) The semiconductor body of claim 6 wherein said trench is oval shaped.
16. (New) The semiconductor body of claim 1 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.

17. (New) The semiconductor body of claim 5 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.
18. (New) The semiconductor body of claim 6 wherein said trench comprises a capacitor in a lower portion and a FET in an upper portion to form a DRAM cell.